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TriQSiC™ 1200V Silicon Carbide Schottky Diode G1

Features

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Benefits

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Applications

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Table 1 Key performance and package parameters

Type	V_{RRM}	I_F	Q_C	Marking	Package

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Features **1**

Benefits **1**

Applications **1**

Table of contents **2**

1 Maximum ratings **3**

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1 Maximum ratings

Table 2 Maximum rating le

Symbol	Parameter	Value	Unit	Test Conditions	Note

3 Electrical characteristics

Table 4 Electrical characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note

4 Electri

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